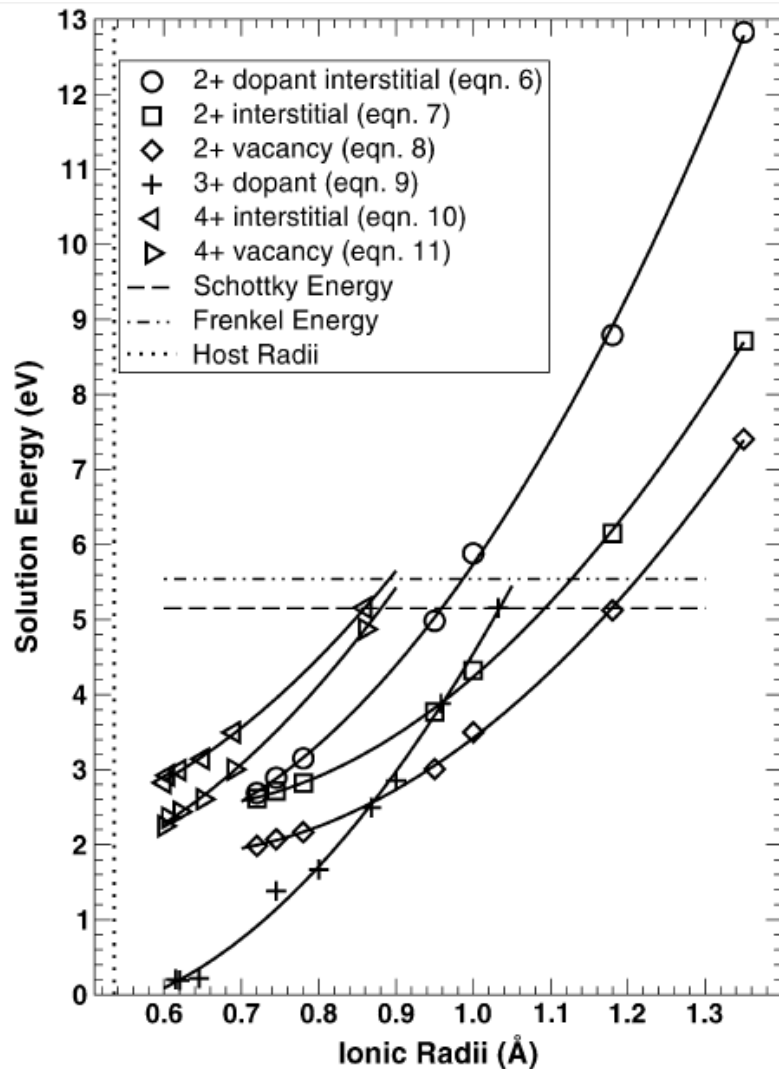


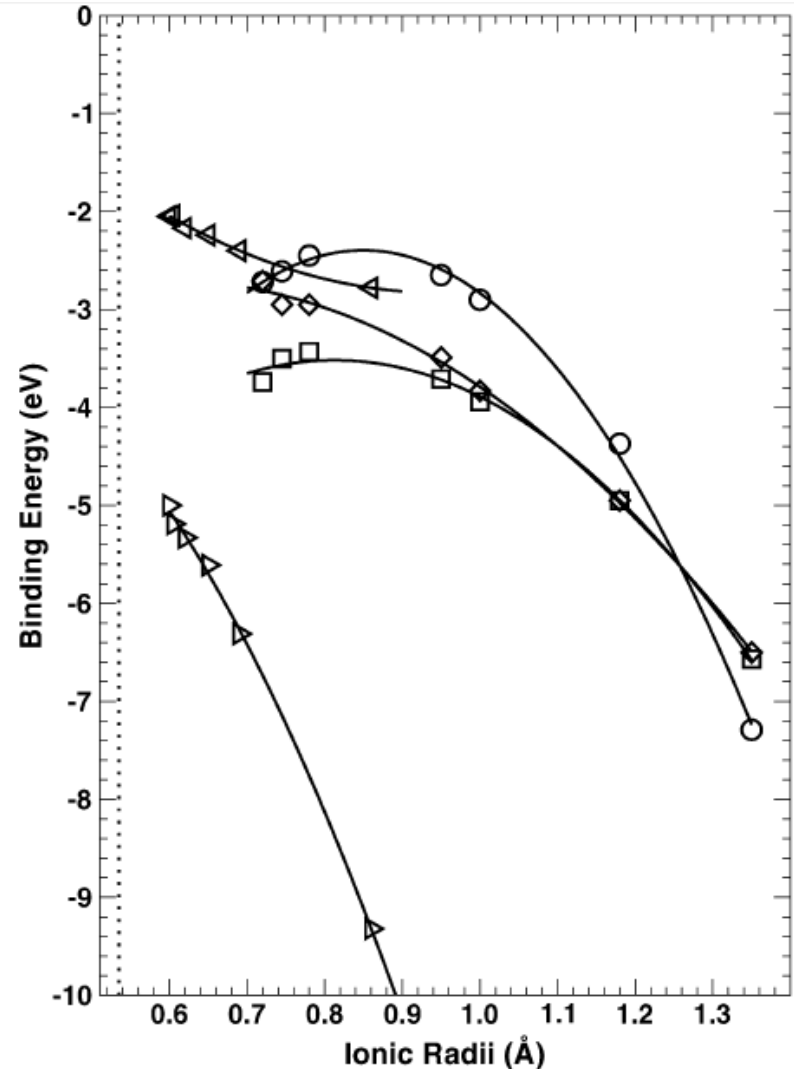
Research in Next 6-12 Months

- G.B. thermal conductance in doped samples
 - Bi crystals
 - Polycrystals
- Continue Diffusion in Al_2O_3 (Cr^{3+} , O^{2-} , 18)
 - Approximate ΔS
- Diffusion in Ni-W
 - Borisov Model $\Delta H_{\text{GB}} \sim \Delta H_{\text{L}} - \gamma$ (w/o complexions)
 - Complement Lehigh/Clemson-UCSD work

Defects in Alumina

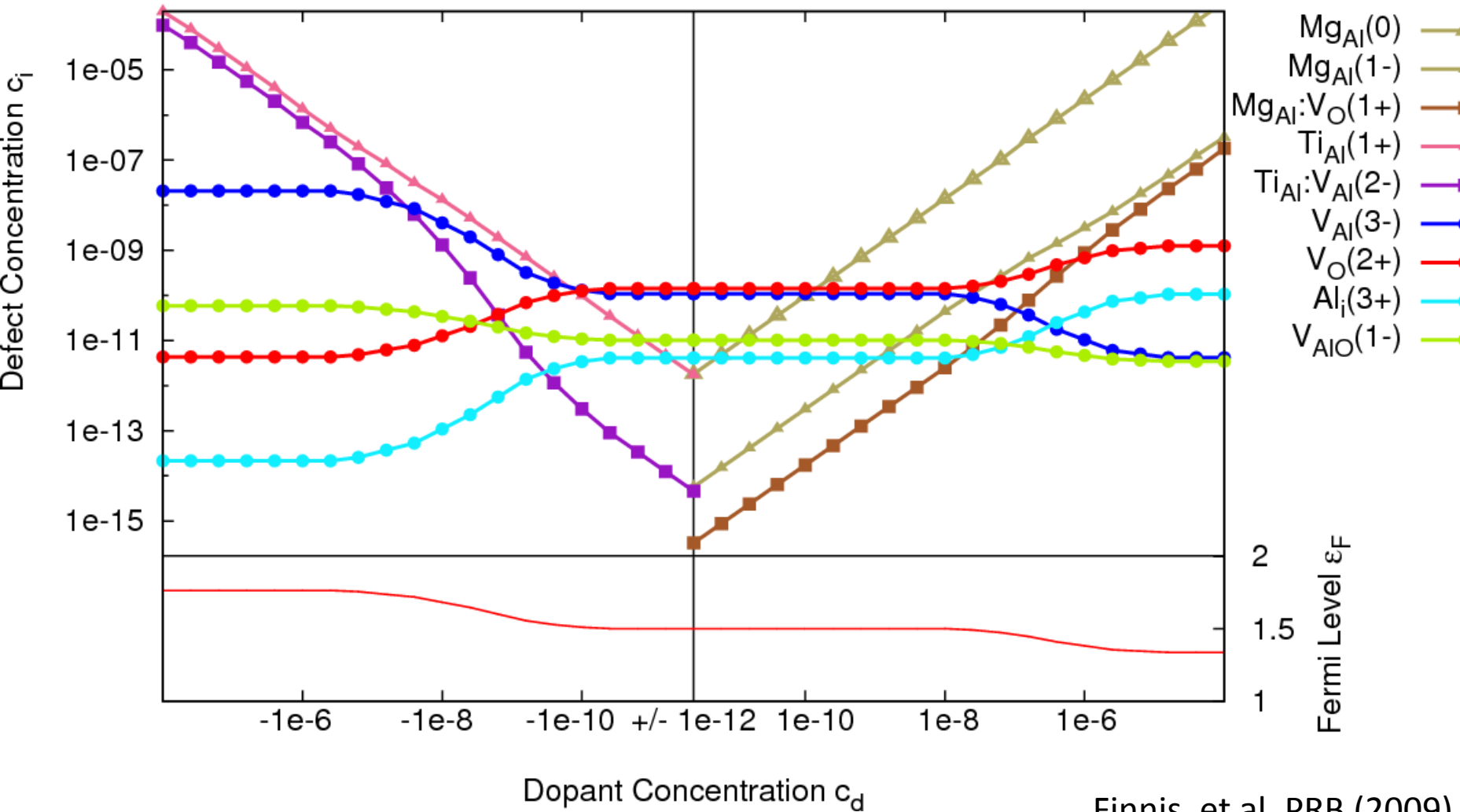


(a) Isolated Solution Energies



(b) Cluster Binding Energies

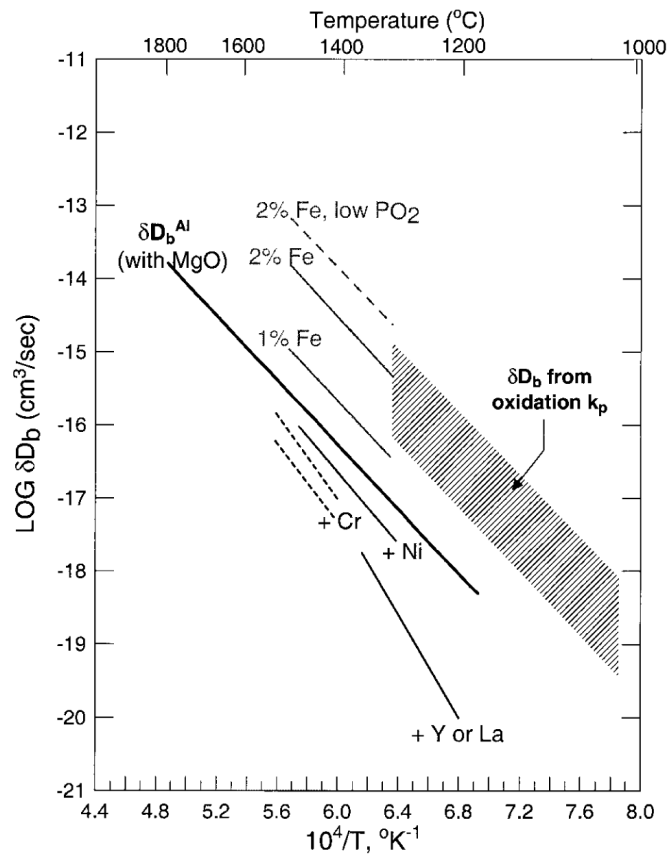
Defects in Alumina



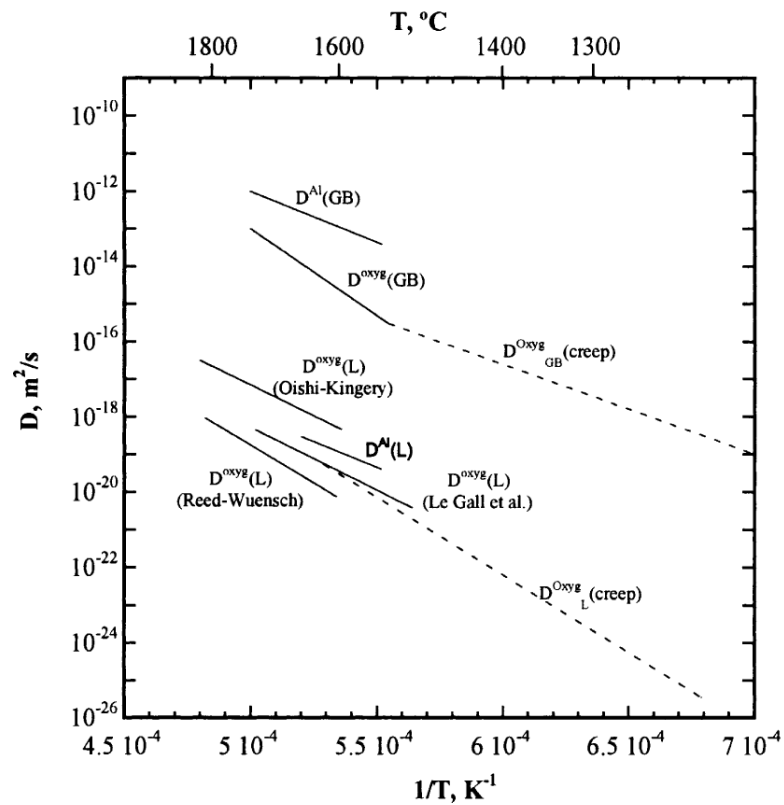
Finnis, et al. PRB (2009)

Fraction of mobile defects in Si^{4+} at 1400 $\sim 10^{-11}$

P. Hou



O. Ruano, J. Wadsworth, and O. Sherby



Alumina Diffusion - Motivation

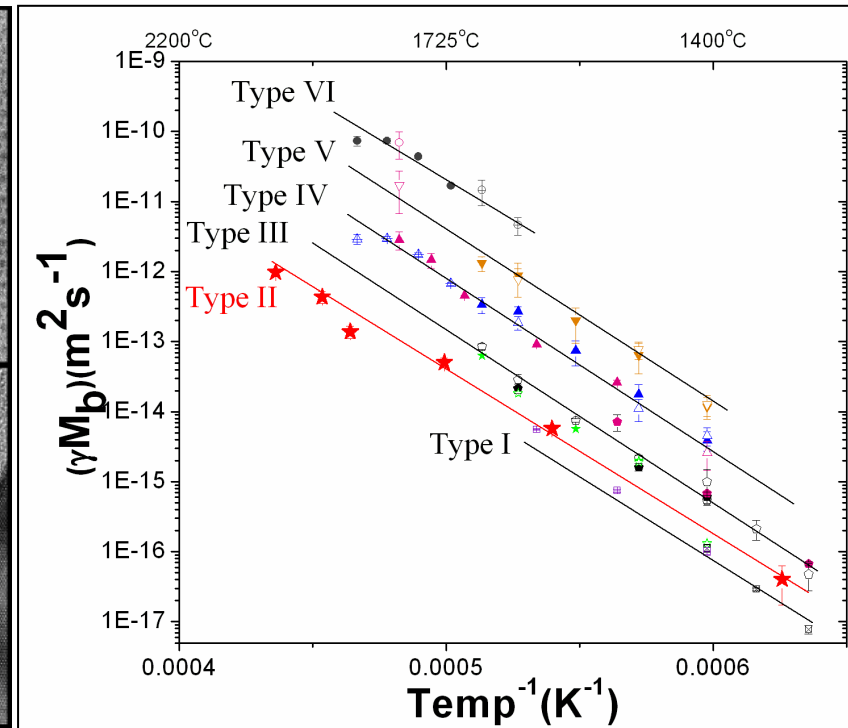
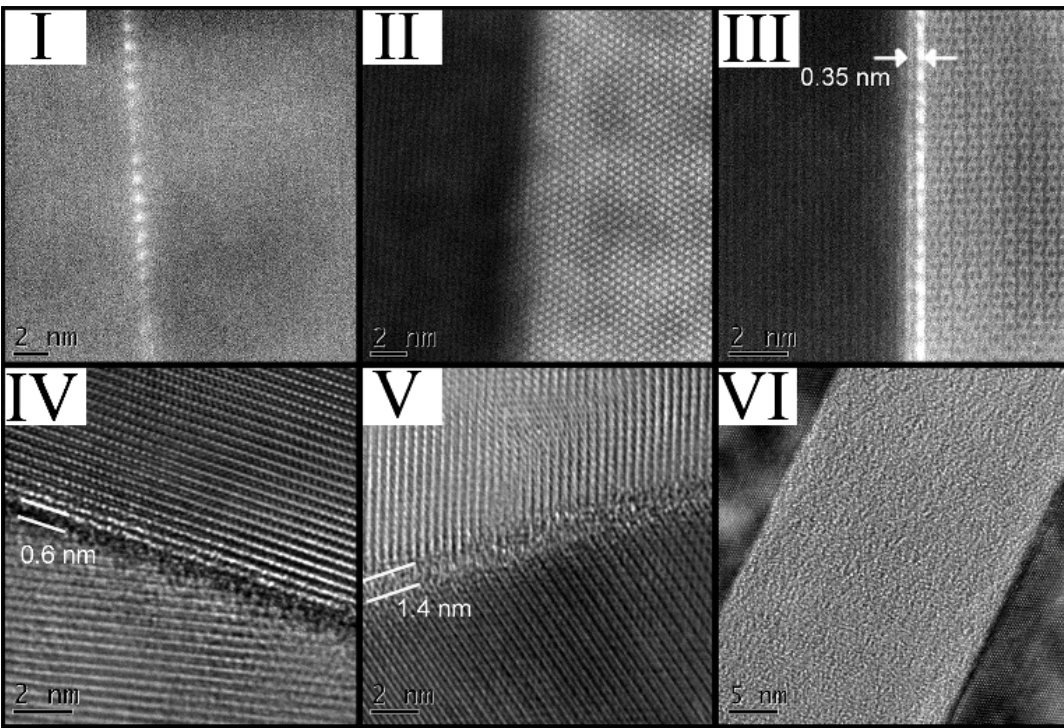
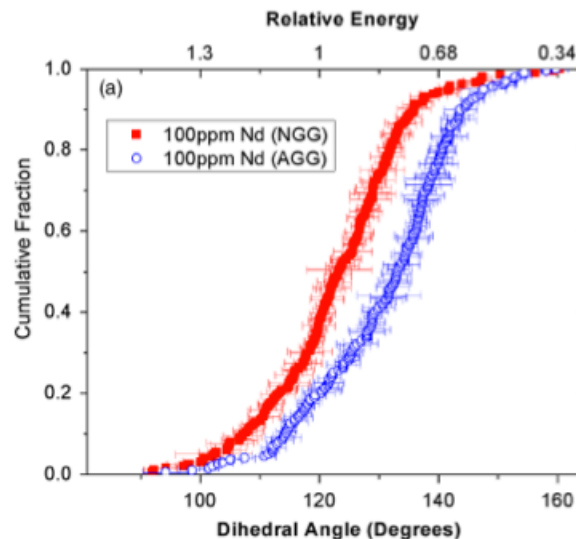
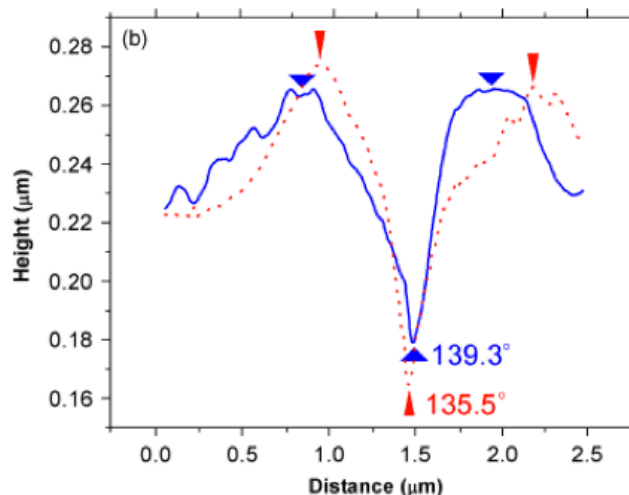
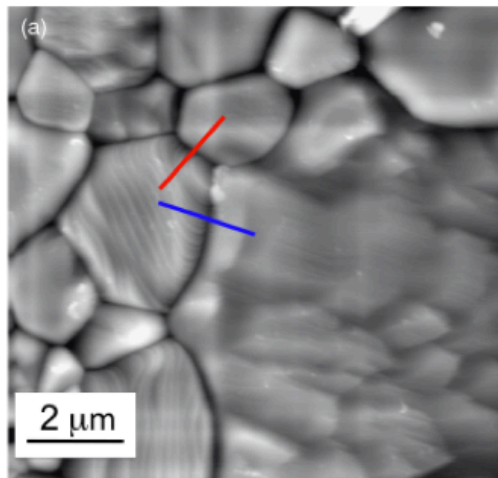


Table I. The Mean Relative Energies of Different Grain-Boundary Complexions Occurring as Normal and Abnormal Grains in Doped and Undoped Alumina Annealed at Different Temperatures

Chemistry	Temperature (°C)	Complexion	Relative energy	% energy change (complexion transition)
Undoped	1400	II (NGG)	1.11	
	2020	II (NGG)	1.08	
100 ppm-Nd ₂ O ₃	1400	I (NGG)	0.95	-16
	1400	III (AGG)	0.8	
100 ppm-Y ₂ O ₃	1400	I (NGG)	0.57	-46
	1400	III (AGG)	0.31	
500 ppm-MgO	1400	I (NGG)	1.07	-26
	1700	III (NGG)	0.79	
30 ppm-CaO	1200	I (NGG)	0.82	-20
	1200	III (AGG)	0.69	
200 ppm-SiO ₂	1200	I (NGG)	0.68	-10
	1200	III (AGG)	0.61	

Relative Grain Boundary Energies

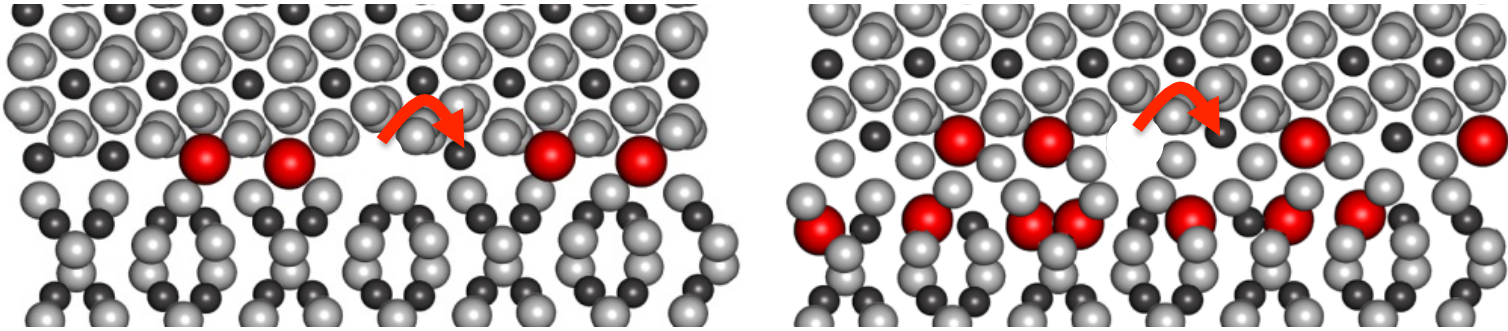


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	1200	III (AGG)	0.61	
30 ppm-CaO	1400	III (NGG)	1.02	0.1
	1400	IV+ (AGG)	1.02	
200 ppm-SiO ₂	1400	III (Basal plane)	0.77	
	1400	III (NGG)	0.65	9.5
200 ppm-SiO ₂	1400	IV (AGG)	0.71	
	1750	IV (NGG)	0.98	-1.7
	1750	V+ (AGG)	0.96	

Dillon et al. *JACerS* (2012)

Rohrer et al. continuing more detailed analysis

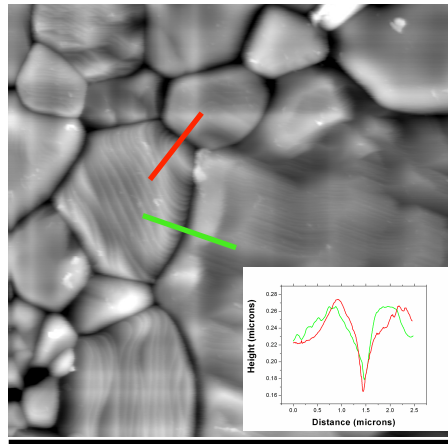
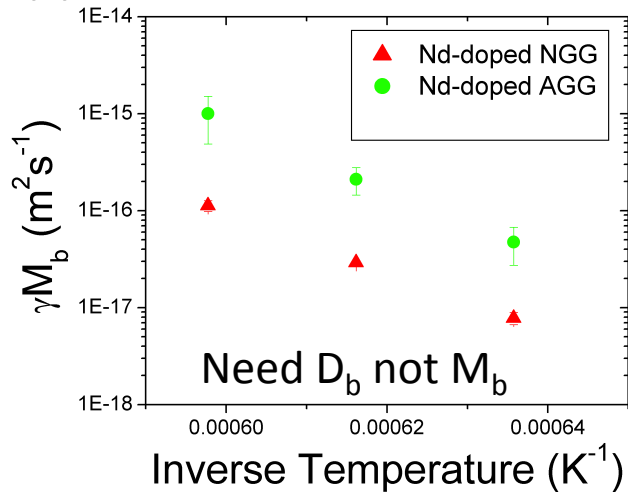
Comparing Complexions (ΔH & ΔS)



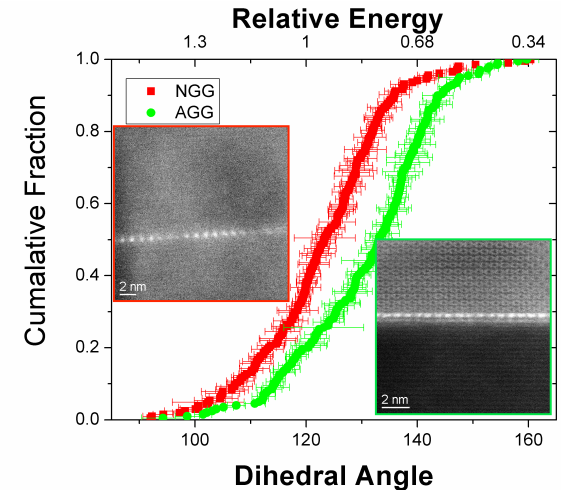
$$\Delta\gamma = \Delta\rho [RT \ln(ga_{\perp}^2 v_{\perp}^* / g\kappa_{\parallel} a_{\parallel}^2 v_{\parallel}^*) - T(\Delta S_{f,\perp} - \Delta S_{f,\parallel}) + (\Delta H_{f,\perp} - \Delta H_{f,\parallel}) + (\Delta H_{m,\perp} - \Delta H_{m,\parallel})]$$

Simplifying Assumptions: $\Delta\gamma = \Delta\rho [-T(\Delta S_{\perp} - \Delta S_{\parallel}) + (\Delta H_{\perp} - \Delta H_{\parallel})]$

Approach:

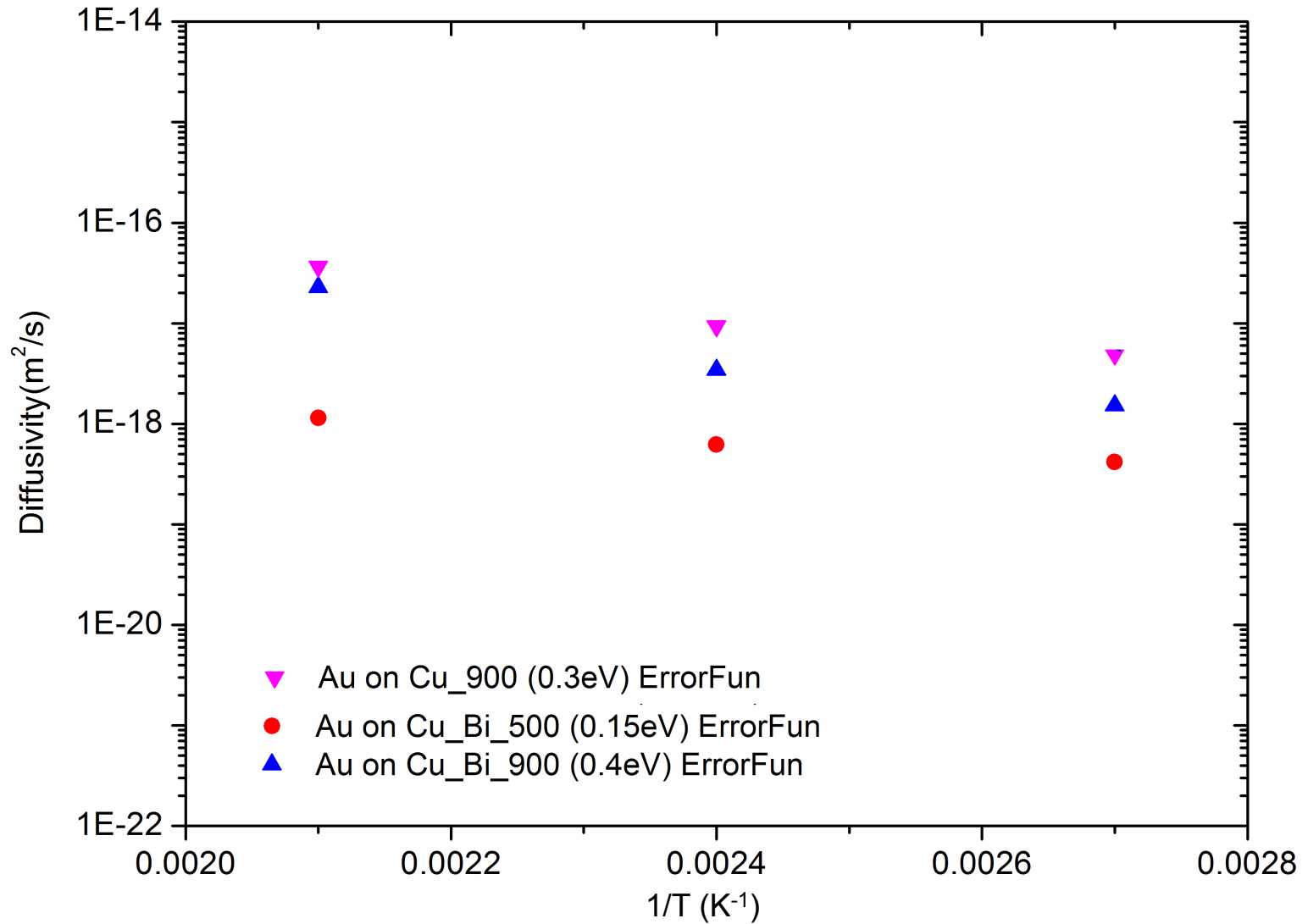


10 micron



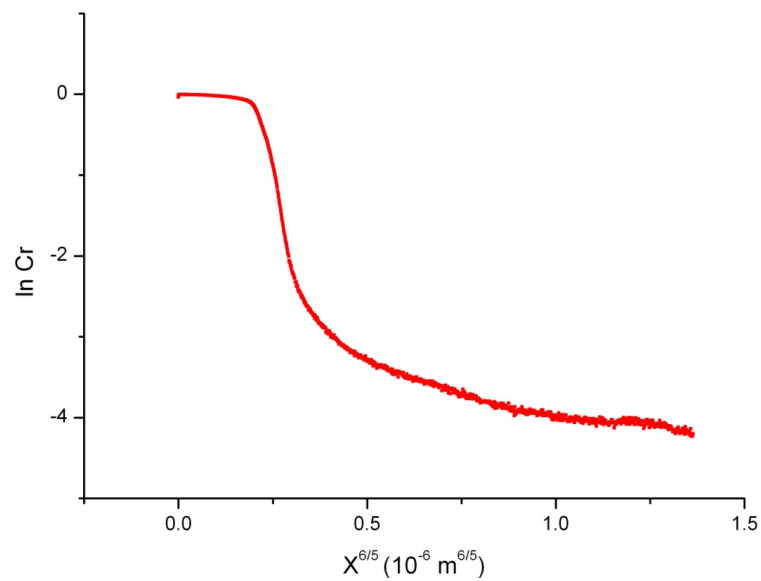
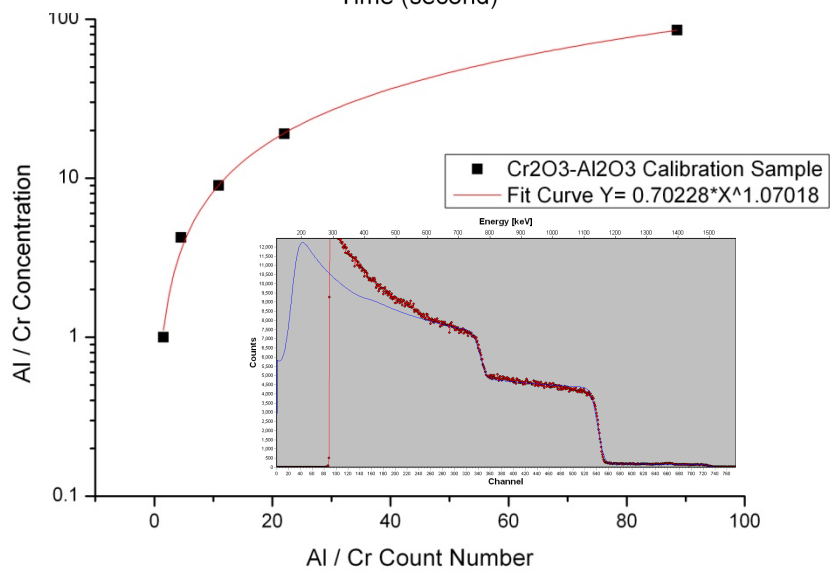
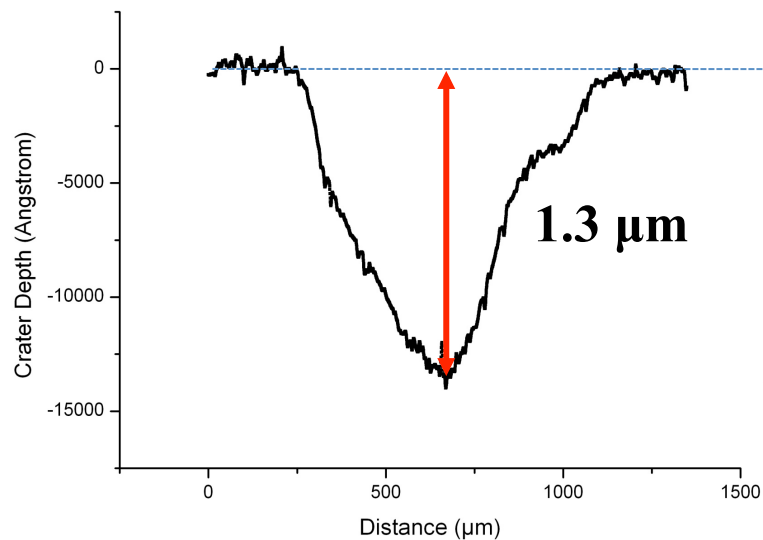
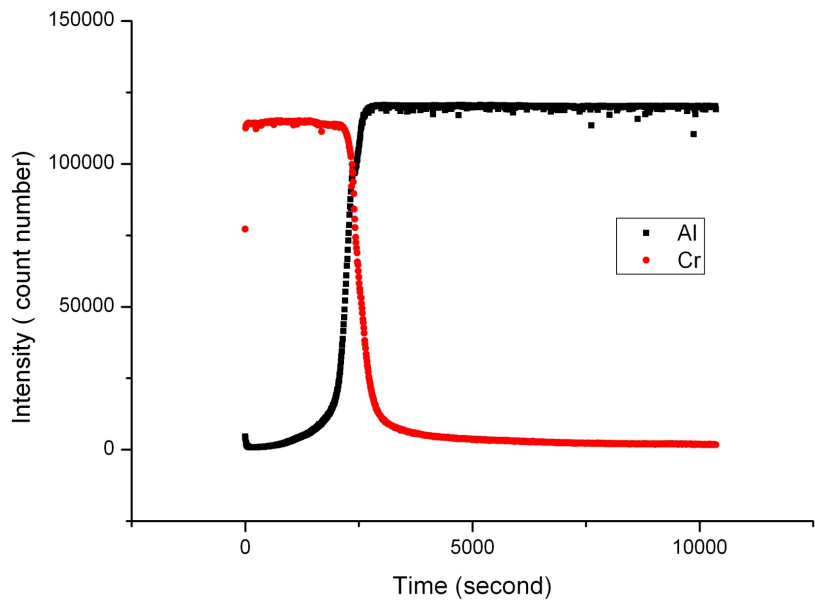
Check: $\gamma = \rho [RT \ln(ga_b^2 v_b^* / g\kappa_a a_a^2 v_a^*) - T(\Delta S_{\perp} - \Delta S_b) + (\Delta H_{\perp} - \Delta H_b) + (P\Delta V_{\perp} - P\Delta V_b)]$

Diffusion in Bi doped Cu

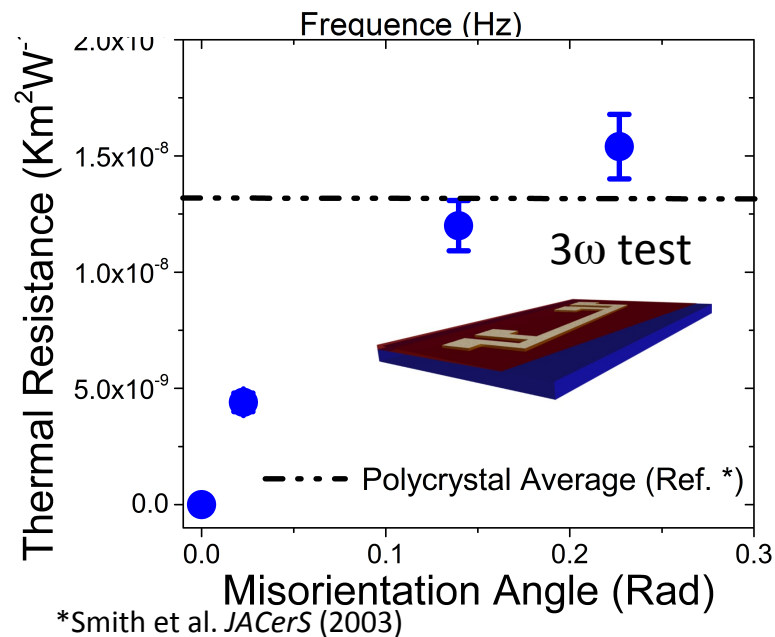
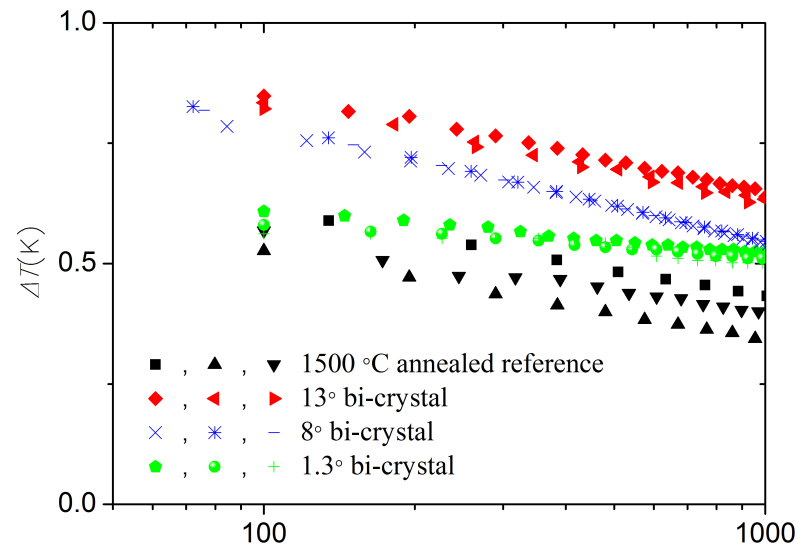
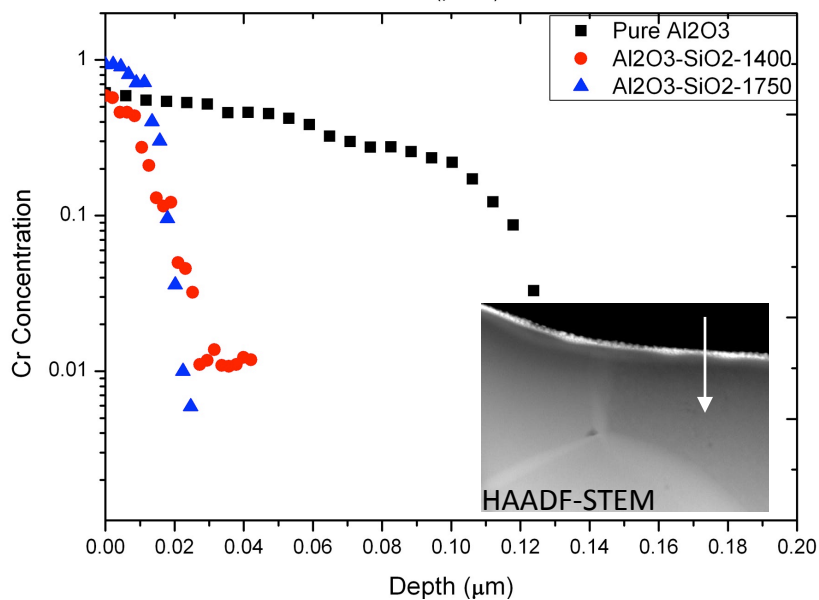
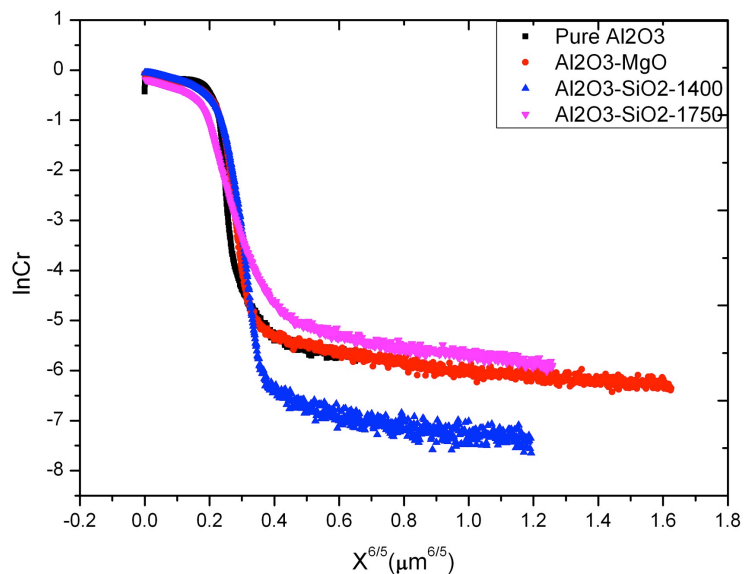


Au diffusivity-temperature dependence in the Cu(Bi) alloys

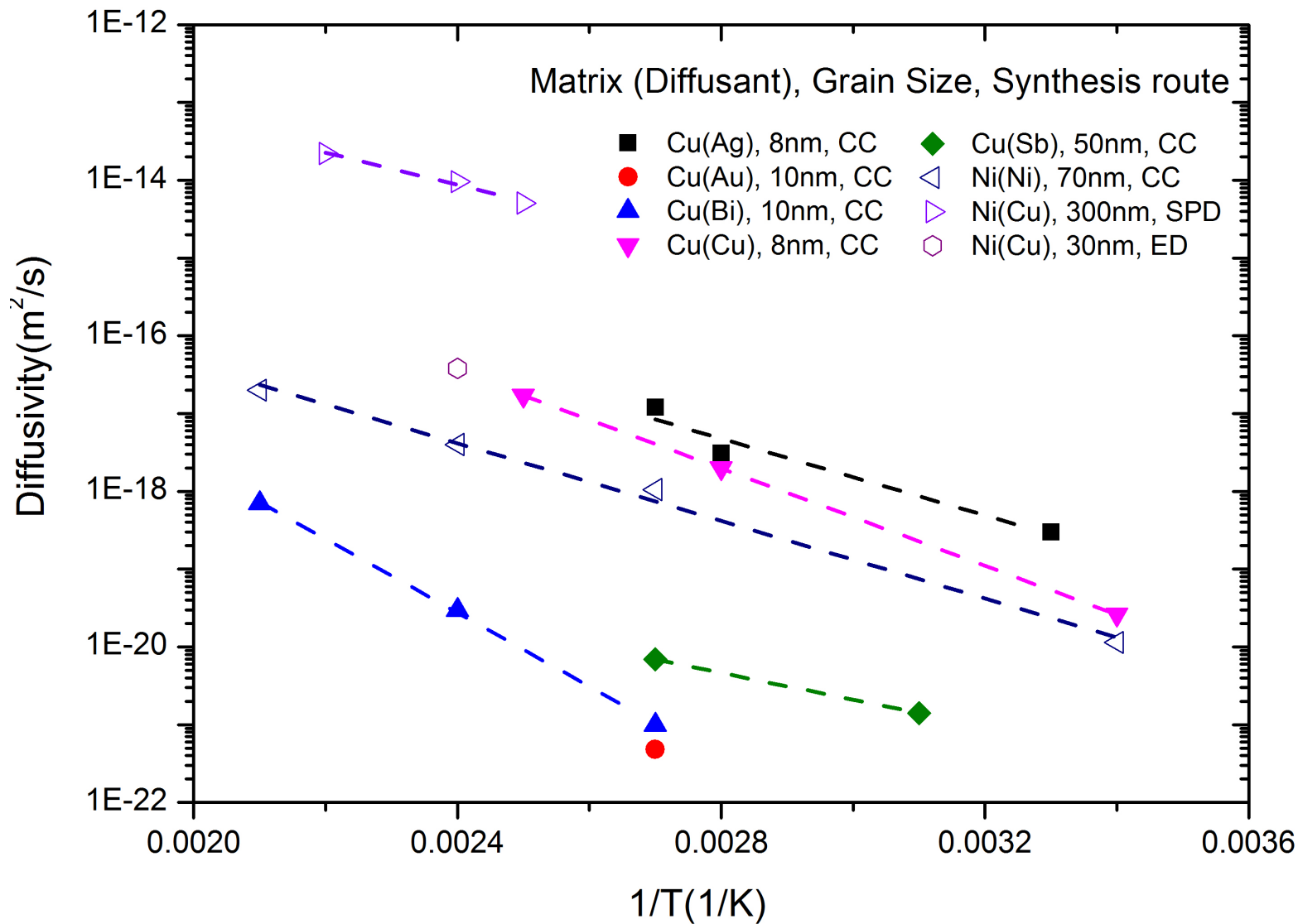
Cr³⁺ Diffusion in Al₂O₃



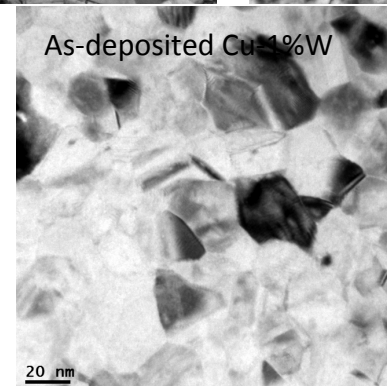
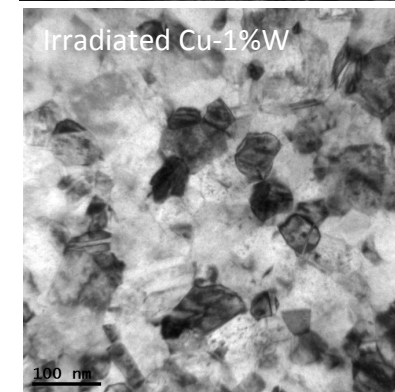
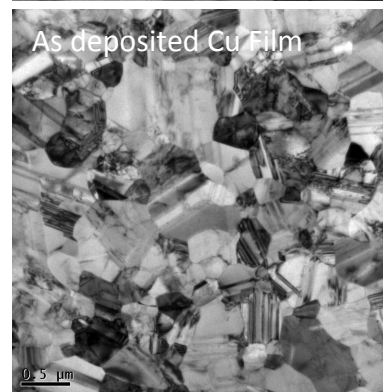
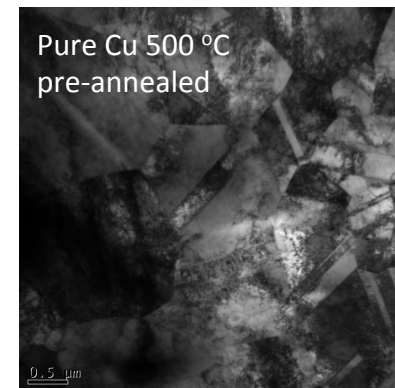
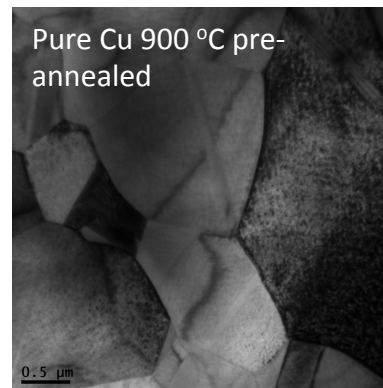
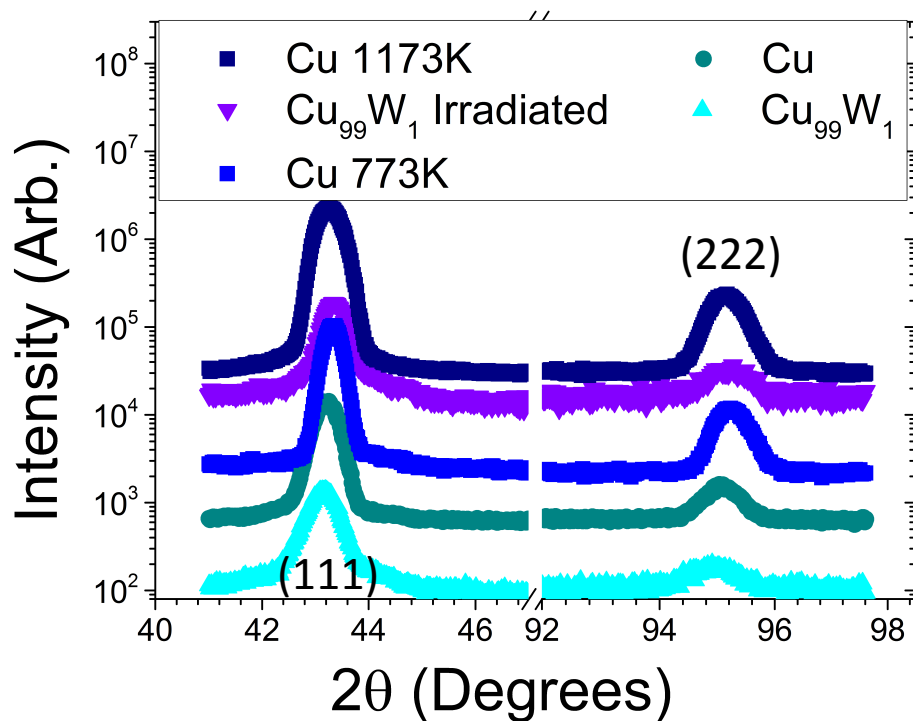
Continued Work: Obtaining D , γ , T_c in Al_2O_3 (then V^*)



GB Diffusion Nanograin Alloys- Motivation

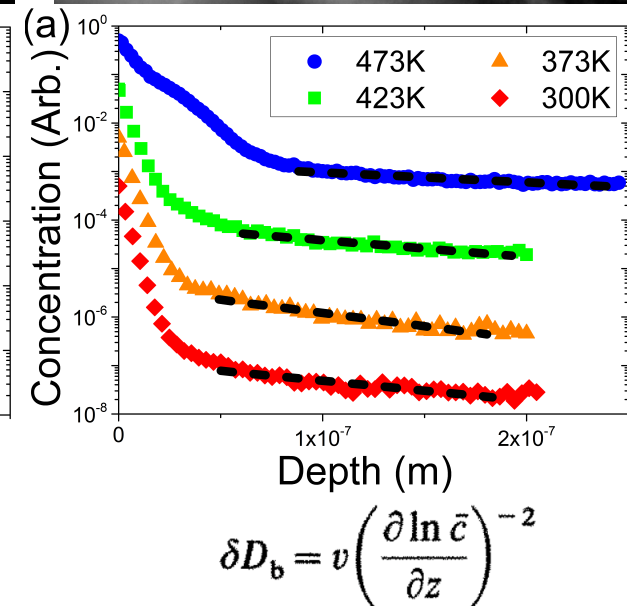
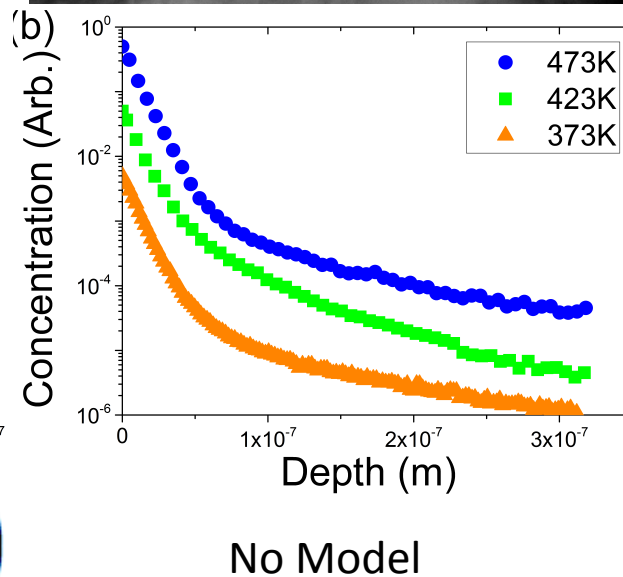
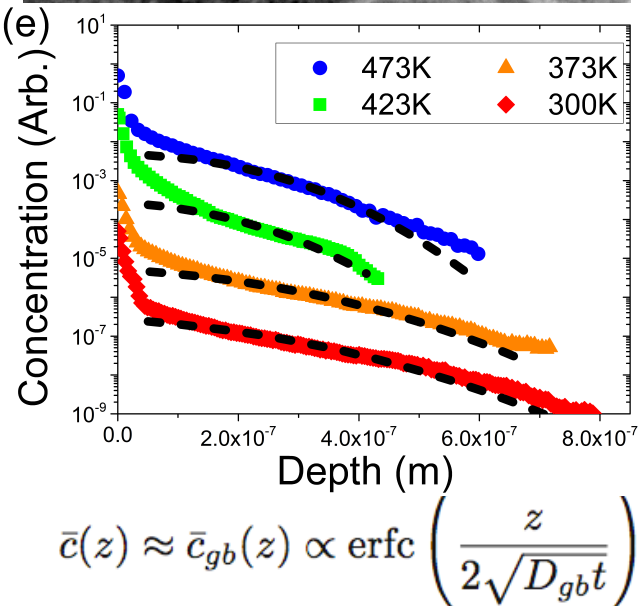
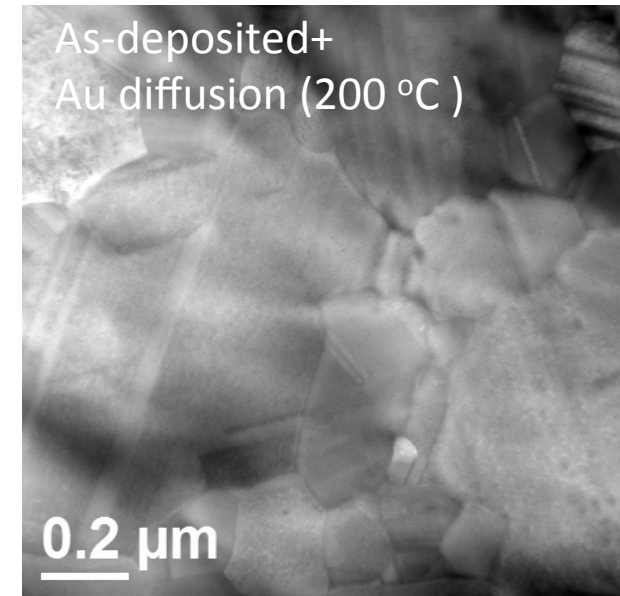
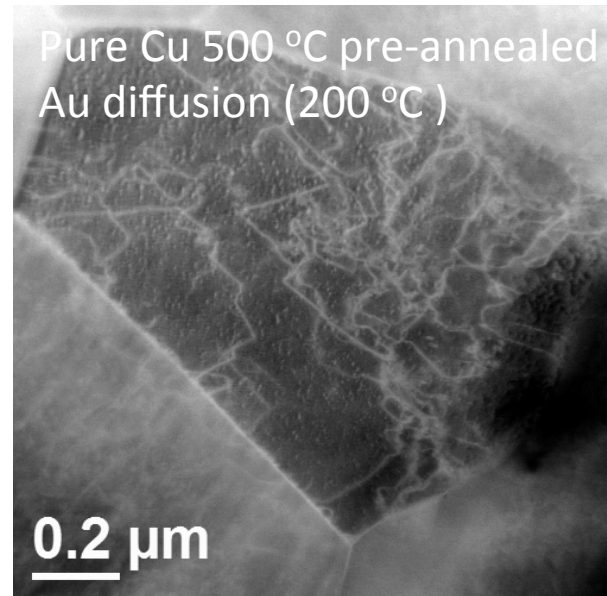
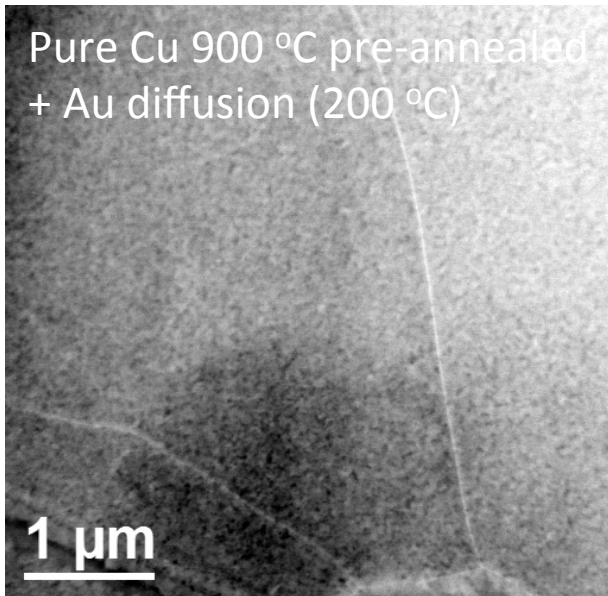


Cu of Varying Grain Size

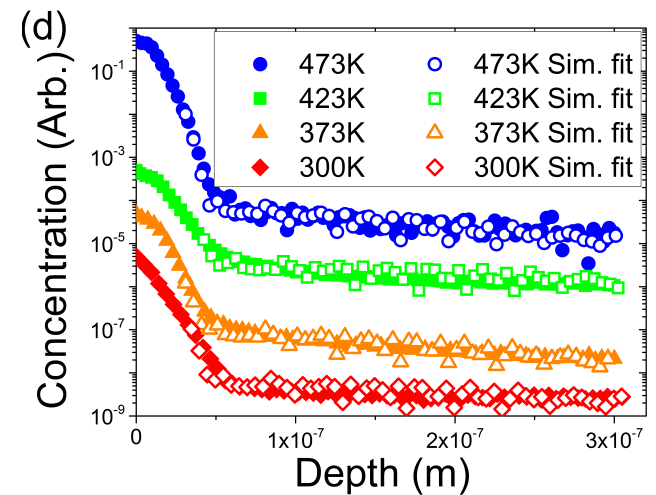
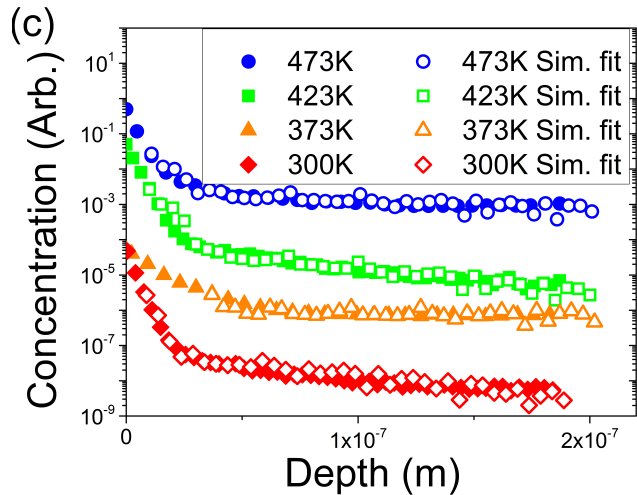
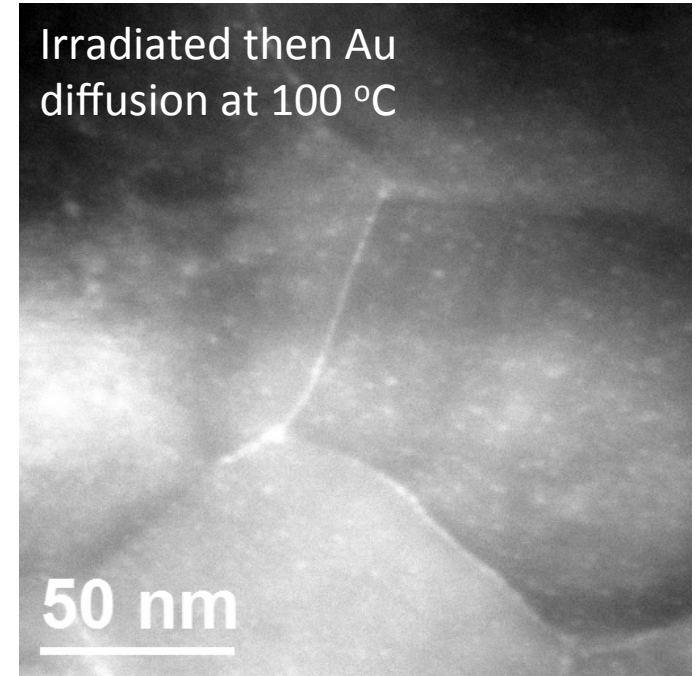
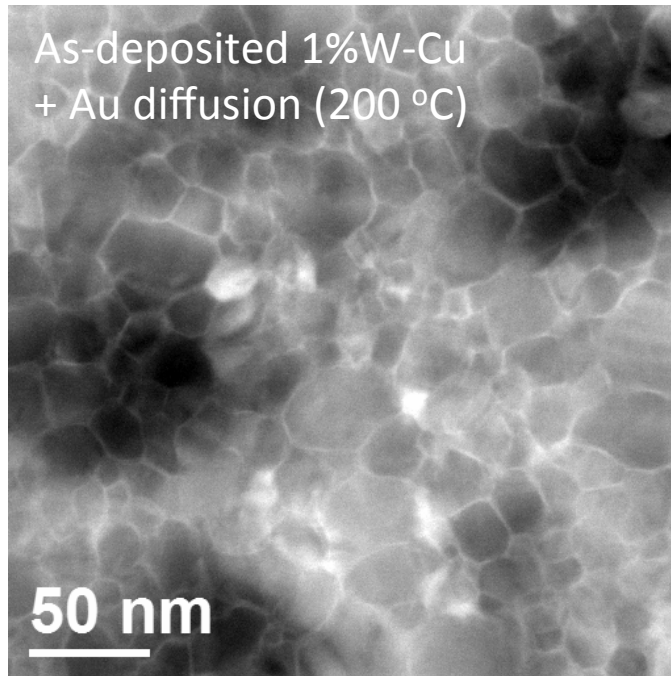


Sample	Average Grain Size (nm)		
	X-ray	TEM	
		w/o twins	w/ twins
Cu	15.0	~150	~20
Cu-W	14.7	~30	~15
Irrad. Cu-W	17.0	~80	~25
773K Cu	23.5	~2000	~280
1173K Cu	47.0	~4000	~550

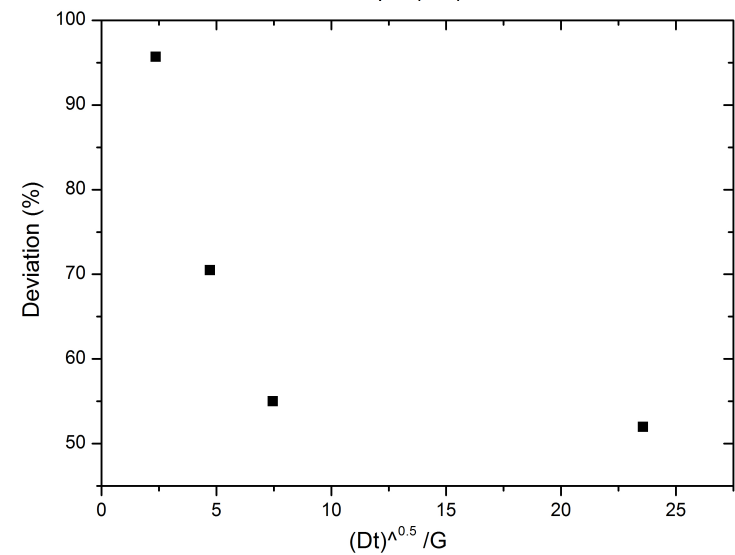
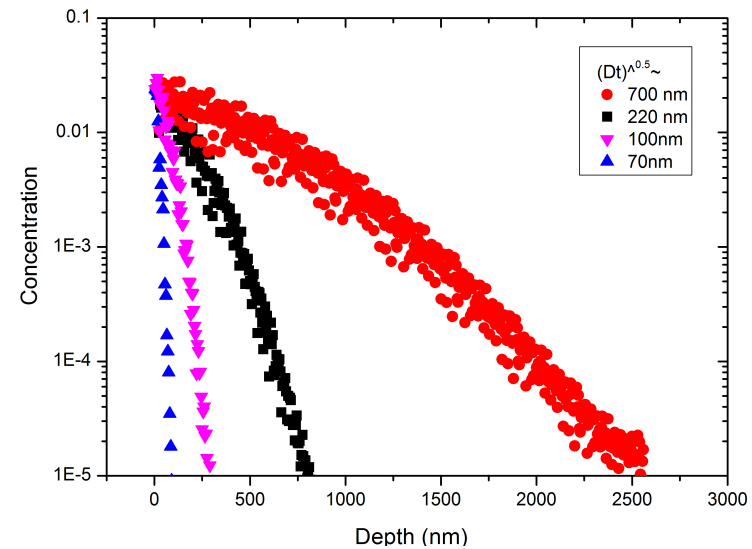
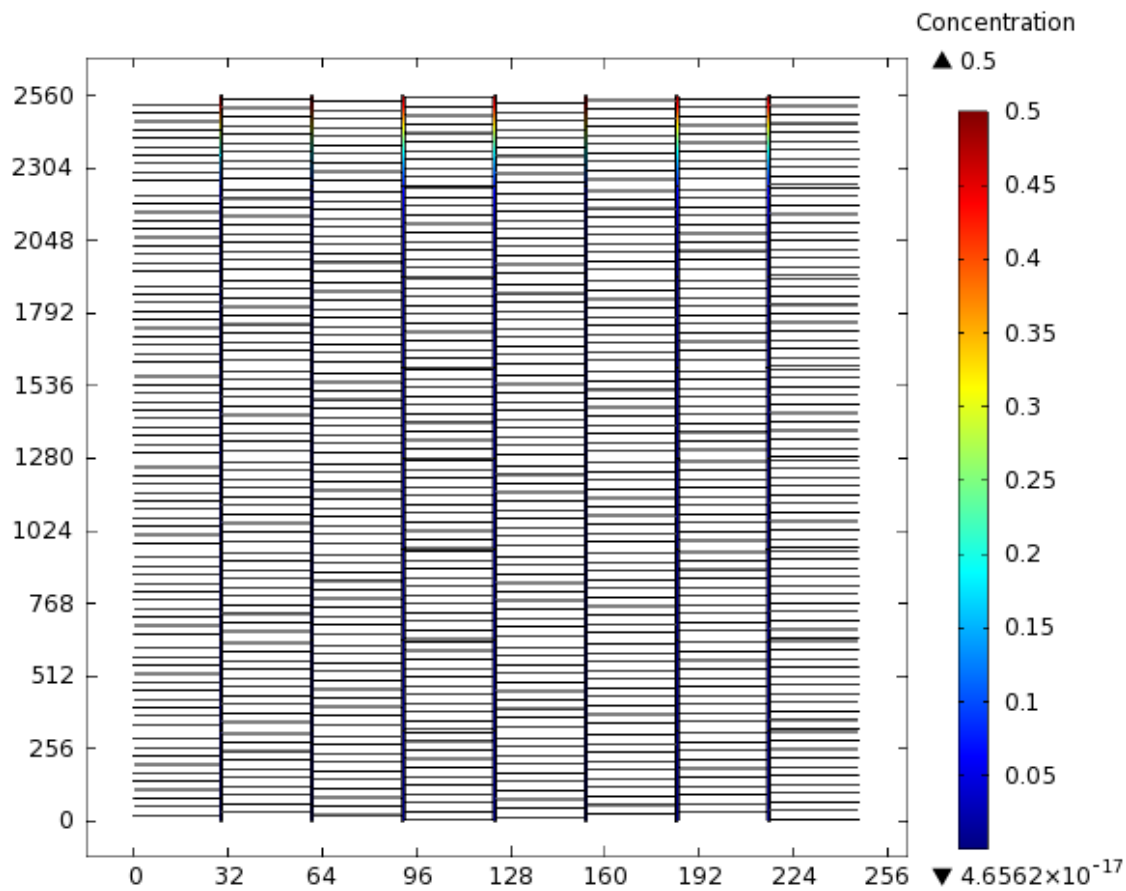
Au diffusion in Cu (Different G.S.'s)



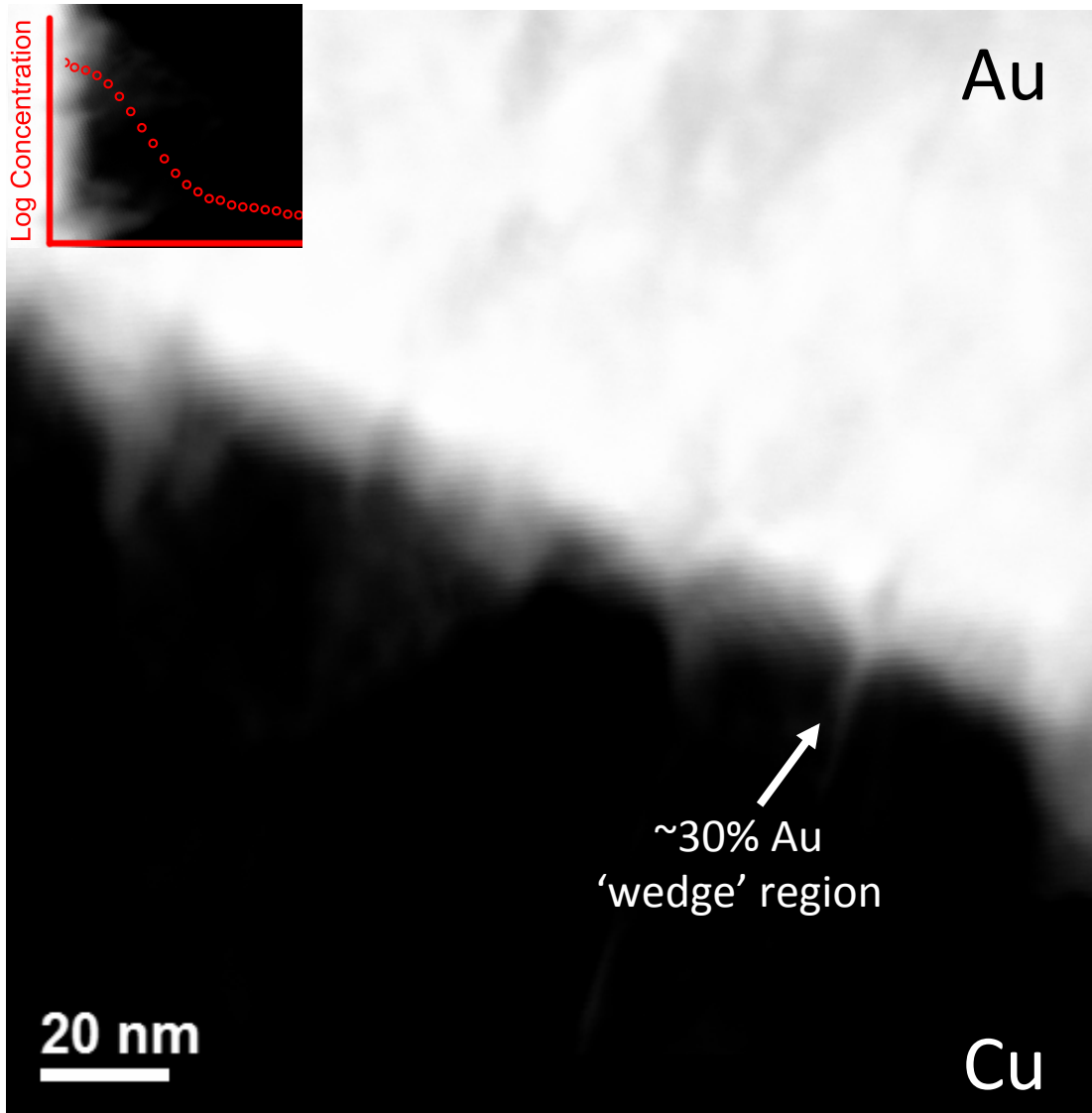
Au diffusion in Cu (Different G.S.'s)



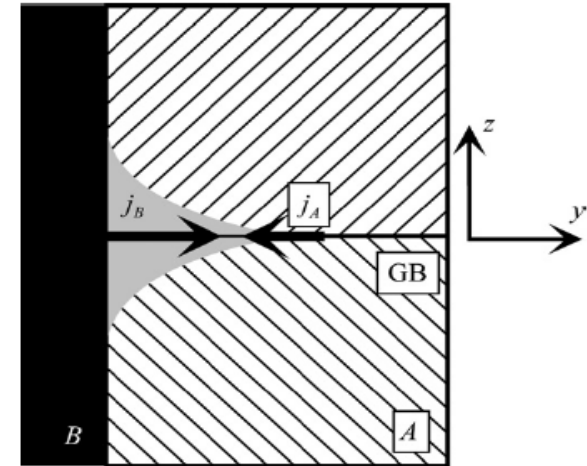
FE Simulation Nanograin Diffusion



Grain Boundary Kirkendall Effect



Kirkendall Effect induced
G.B. migration/lattice drift



A-B

Inequality Diffusion

$$j_A = -\frac{D_A n_A}{kT} \frac{\partial \mu_A}{\partial y}; \quad j_B = -\frac{D_B n_B}{kT} \frac{\partial \mu_B}{\partial y},$$

$$\frac{\partial C_B}{\partial t} = D_B \frac{\partial^2 C_B}{\partial y^2} + \frac{D_B C_B \Omega}{kT} \frac{\partial^2 \sigma}{\partial y^2} + \frac{\Omega D_B}{kT} \frac{\partial C_B}{\partial y} \frac{\partial \sigma}{\partial y}$$

Finite Element Simulation

Grain boundary diffusion in thin film model:

Near surface (10~20nm) D_{sb} different from D_b in film

